

Abstract of the Disclosure

In a semiconductor optical modulator of this invention, each quantum-well layer and each barrier layer of a quantum-well structure serving as a light absorption layer are respectively made of $\text{In}_{1-x-y}\text{Ga}_x\text{Al}_y\text{N}$ (5 $0 \leq x, y \leq 1, 0 \leq x + y \leq 1$) and $\text{In}_{1-x'-y'}\text{Ga}_{x'}\text{Al}_{y'}\text{N}$ ($0 \leq x', y' \leq 1, 0 \leq x' + y' \leq 1$). An electric field is being generated in the light absorption layer by spontaneous polarization.